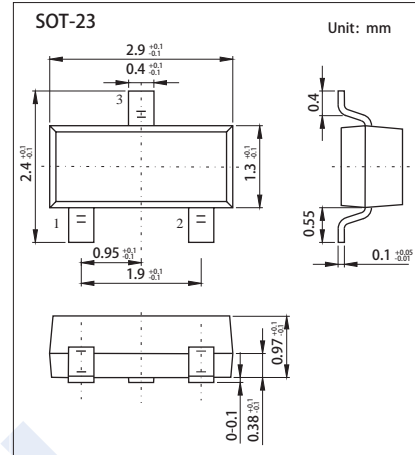
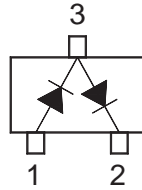


Switching Diodes

1KS3009

■ Features

- Fast Switching Speed
- For General Purpose Switching Applications.
- High Conductance

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Repetitive Peak Reverse Voltage	V_{RRM}	120	V	
Continuous Reverse Voltage	V_R	120		
Forward Current	I_F	200	mA	
Repetitive Peak Forward Current	I_{FRM}	600		
Non-repetitive Peak Forward Surge Current	I_{FSM}	$t=1\text{s}$	1.0	A
		$t=1\text{ms}$	1.5	
		$t=1\mu\text{s}$	2.0	
Power Dissipation	P_d	350	mW	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature range	T_{stg}	-55 to 150		

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100\ \mu\text{A}$	120			V
Forward voltage	V_F	$I_F = 1\ \text{mA}$			0.715	
		$I_F = 10\ \text{mA}$			0.855	
		$I_F = 50\ \text{mA}$			1	
		$I_F = 150\ \text{mA}$			1.25	
Reverse voltage leakage current	I_R	$V_R = 25\ \text{V}$			30	nA
		$V_R = 90\ \text{V}$			100	
		$V_R = 25\ \text{V}, T_J = 150^\circ\text{C}$			30	uA
		$V_R = 90\ \text{V}, T_J = 150^\circ\text{C}$			50	
Junction capacitance	C_j	$V_R = 0\ \text{V}, f = 1\ \text{MHz}$			1.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\ \text{mA}, I_R = 1\ \text{mA}, R_L = 100\ \Omega$			50	ns

■ Marking

Marking	SS9
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Switching Diodes

1KS3009

■ Typical Characteristics

